2SB1219G

Silicon PNP epitaxial planar type

For general amplification

Complementary to 2SD1820G

Features

- \bullet Large collector current $I_{\rm C}$
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Emitter-base voltage (Collector open)	V _{EBO}	-5	V	
Collector current	I _C	-500	mA	
Peak collector current	I _{CP}	-1	А	
Collector power dissipation	P _C	150	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

- Package
- Code
- SMini3-F2
- Marking Symbol: D
- Pin Name
 - 1. Base
 - 2. Emitter
 - 3. Collector

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu A, I_{\rm E} = 0$	-60	0	C C	V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50		2	V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = -10 \ \mu A, I_{\rm C} = 0$	-5	S		V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$	s S	0	- 0.1	μΑ
Forward current transfer ratio *1	h _{FE1} *2	$V_{CE} = -10 \text{ V}, I_C = -150 \text{ mA}$	85		340	
	h _{FE2}	$V_{CE} = -10 \text{ V}, I_C = -500 \text{ mA}$	40			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_{\rm C} = -300 \text{ mA}, I_{\rm B} = -30 \text{ mA}$		- 0.35	- 0.60	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_{\rm C} = -300 \text{ mA}, I_{\rm B} = -30 \text{ mA}$		-1.1	-1.5	V
Transition frequency	f _T	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		6	15	pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

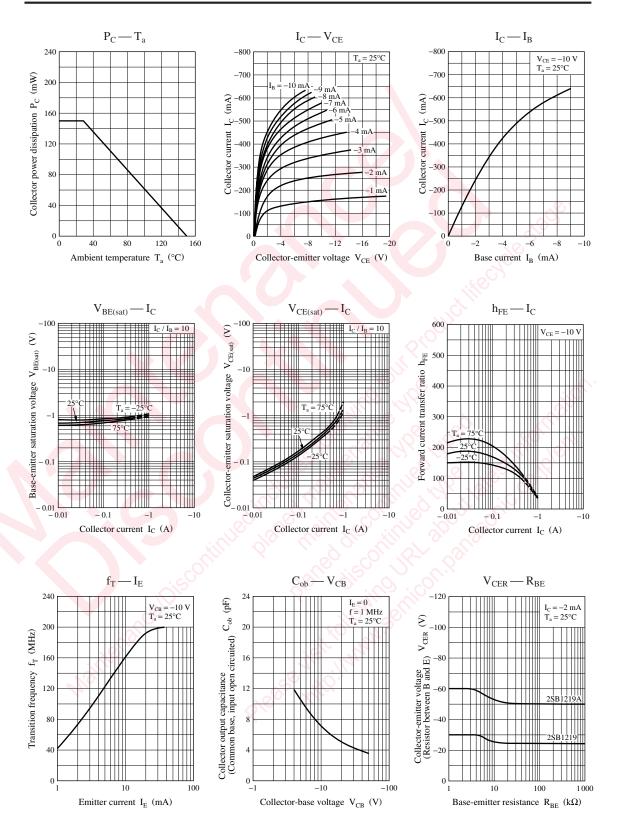
2. *1: Pulse measurement

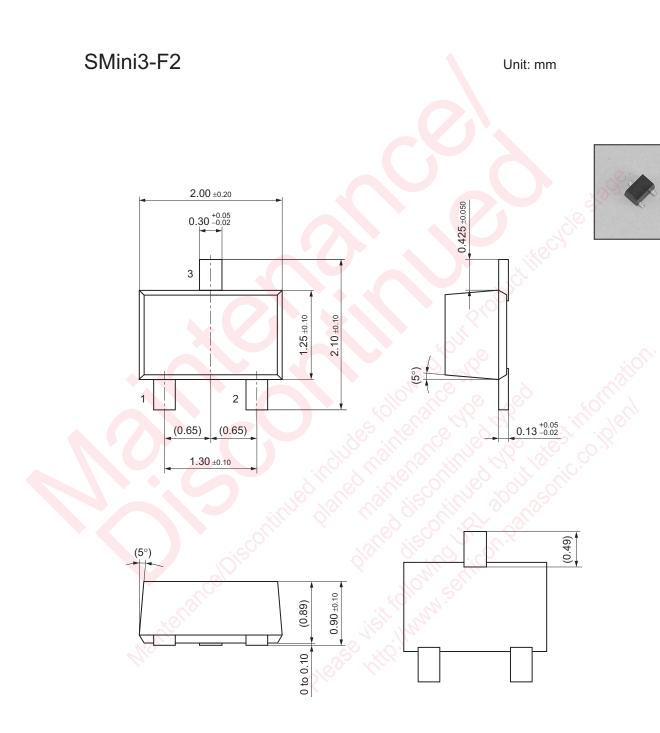
*2: Rank classification

Rank	Q	R	S	No-rank
h _{FE1}	85 to 170	120 to 240	170 to 340	85 to 340
Marking symbol	DQ	DR	DS	D

Note) Product of no-rank is not classified and have no marking symbol for rank.

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